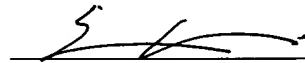


REMARKS

Claims 2-6, 8-12, 14-18, 20-24, 26-55 have been amended to correct minor typographical matters and new claims 56-130 have been added in this application to complete the scope of applicants' protection. New claims 56-130 do not include a limitation of an interlayer insulating film on the thin film transistor.

Examination on the merits is requested.

Respectfully submitted,



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VERSION WITH MARKINGS TO SHOW CHANGES MADE

2. (Amended) A display device according to claim 1 wherein said semiconductor film comprises crystalline silicon.

3. (Amended) A display device according to claim 1 wherein said thin film transistor further comprises a gate electrode located over said semiconductor film with a gate insulating film interposed therebetween.

4. (Amended) A display device according to claim 1 wherein said organic resin comprises polyimide.

5. (Amended) [The device of] A display device according to claim 1 wherein said pixel electrode comprises a transparent conductive film.

6. (Twice Amended) [The device of] A display device according to claim 1 wherein said display is a digital gradation display.

8. (Amended) A display device according to claim 7 wherein said semiconductor film comprises crystalline silicon.

9. (Amended) A display device according to claim 7 wherein said thin film transistor further comprises a gate electrode located over said semiconductor film with a gate insulating film interposed therebetween.

10. (Amended) A display device according to claim 7 wherein said organic resin comprises polyimide.

11. (Amended) [The device of] A display device according to claim 7 wherein said pixel electrode comprises a transparent conductive film.

12. (Twice Amended) [The device of] A display device according to claim 7 wherein said display is a digital gradation display.

14. (Amended) A display device according to claim 13 wherein said semiconductor film comprises crystalline silicon.

15. (Amended) A display device according to claim 13 wherein said thin film transistor further comprises a gate electrode located over said semiconductor film with a gate insulating film interposed therebetween.

16. (Amended) A display device according to claim 13 wherein said organic resin comprises polyimide.

17. (Amended) [The device of] A display device according to claim 13 wherein said pixel electrode comprises a transparent conductive film.

18. (Twice Amended) [The device of] A display device according to claim 13 wherein said display is a digital gradation display.

20. (Amended) A display device according to claim 19 wherein said semiconductor film comprises crystalline silicon.

21. (Amended) A display device according to claim 19 wherein said thin film transistor further comprises a gate electrode located over said semiconductor film with a gate insulating film interposed therebetween.

22. (Amended) A display device according to claim 19 wherein said organic resin comprises polyimide.

23. (Amended) [The device of] A display device according to claim 19 wherein said pixel electrode comprises a transparent conductive film.

24. (Twice Amended) [The device of] A display device according to claim 19 wherein said display is a digital gradation display.

26. (Amended) A display device according to claim 25 wherein said semiconductor film comprises crystalline silicon.

27. (Amended) A display device according to claim 25 wherein said thin film transistor further comprises a gate electrode located over said semiconductor film with a gate insulating film interposed therebetween.

28. (Amended) A display device according to claim 25 wherein said organic resin comprises polyimide.

29. (Amended) [The device of] A display device according to claim 25 wherein said pixel electrode comprises a transparent conductive film.

30. (Twice Amended) [The device of] A display device according to claim 25 wherein said display is a digital gradation display.

31. (Amended) [The device of] A display device according to claim 1 wherein said display further comprises a tuner for receiving television radio wave to constitute a television.

32. (Amended) [The device of] A display device according to claim 7 wherein said display further comprises a tuner for receiving television radio wave to constitute a television.

33. (Amended) [The device of] A display device according to claim 13 wherein said display further comprises a tuner for receiving television radio wave to constitute a television.

34. (Amended) [The device of] A display device according to claim 19 wherein said display further comprises a tuner for receiving television radio wave to constitute a television.

35. (Amended) [The device of] A display device according to claim 25 wherein said display further comprises a tuner for receiving television radio wave to constitute a television.

36. (Amended) [The device of] A display device according to claim 31 wherein said television is a liquid crystal television.

37. (Amended) [The device of] A display device according to claim 32 wherein said television is a liquid crystal television.

38. (Amended) [The device of] A display device according to claim 33 wherein said television is a liquid crystal television.

39. (Amended) [The device of] A display device according to claim 34 wherein said television is a liquid crystal television.

40. (Amended) [The device of] A display device according to claim 35 wherein said television is a liquid crystal television.

41. (Amended) [The device of] A display device according to claim 1 wherein said thin film transistor has at least one gate electrode adjacent to said

semiconductor film, said gate electrode comprising a material selected from the group consisting of silicon, molybdenum, tungsten, molybdenum silicide, and tungsten silicide.

42. (Amended) [The device of] A display device according to claim 7 wherein said thin film transistor has at least one gate electrode adjacent to said semiconductor film, said gate electrode comprising a material selected from the group consisting of silicon, molybdenum, tungsten, molybdenum silicide, and tungsten silicide.

43. (Amended) [The device of] A display device according to claim 13 wherein said thin film transistor has at least one gate electrode adjacent to said semiconductor film, said gate electrode comprising a material selected from the group consisting of silicon, molybdenum, tungsten, molybdenum silicide, and tungsten silicide.

44. (Amended) [The device of] A display device according to claim 19 wherein said thin film transistor has at least one gate electrode adjacent to said semiconductor film, said gate electrode comprising a material selected from the group consisting of silicon, molybdenum, tungsten, molybdenum silicide, and tungsten silicide.

45. (Amended) [The device of] A display device according to claim 25 wherein said thin film transistor has at least one gate electrode adjacent to said semiconductor film, said gate electrode comprising a material selected from the group consisting of silicon, molybdenum, tungsten, molybdenum silicide, and tungsten silicide.

46. (Amended) [The device of] A display device according to claim 1 wherein a liquid crystal material is formed between said substrate and an opposite substrate, said liquid crystal material selected from the group consisting of a twisted nematic liquid crystal, super twisted nematic liquid crystal, ferroelectric liquid crystal, antiferroelectric liquid crystal, dispersion liquid crystal, and polymer liquid crystal.

47. (Amended) [The device of] A display device according to claim 7 wherein a liquid crystal material is formed between said substrate and an opposite substrate, said liquid crystal material selected from the group consisting of a twisted nematic liquid crystal, super twisted nematic liquid crystal, ferroelectric liquid crystal, antiferroelectric liquid crystal, dispersion liquid crystal, and polymer liquid crystal.

48. (Amended) [The device of] A display device according to claim 13 wherein a liquid crystal material is formed between said substrate and an opposite substrate, said liquid crystal material selected from the group consisting of a twisted nematic liquid crystal, super twisted nematic liquid crystal, ferroelectric liquid crystal, antiferroelectric liquid crystal, dispersion liquid crystal, and polymer liquid crystal.

49. (Amended) [The device of] A display device according to claim 19 wherein a liquid crystal material is formed between said substrate and an opposite substrate, said liquid crystal material selected from the group consisting of a twisted nematic liquid crystal, super twisted nematic liquid crystal, ferroelectric liquid crystal, antiferroelectric liquid crystal, dispersion liquid crystal, and polymer liquid crystal.

50. (Amended) [The device of] A display device according to claim 25 wherein a liquid crystal material is formed between said substrate and an opposite substrate, said liquid crystal material selected from the group consisting of a twisted nematic liquid crystal, super twisted nematic liquid crystal, ferroelectric liquid crystal, antiferroelectric liquid crystal, dispersion liquid crystal, and polymer liquid crystal.

51. (Amended) [The device of] A display device according to claim 1 wherein said semiconductor film comprises silicon or germanium.

52. (Amended) [The device of] A display device according to claim 7 wherein said semiconductor film comprises silicon or germanium.

53. (Amended) [The device of] A display device according to claim 13 wherein said semiconductor film comprises silicon or germanium.

54. (Amended) [The device of] A display device according to claim 19 wherein said semiconductor film comprises silicon or germanium.

55. (Amended) [The device of] A display device according to claim 25 wherein said semiconductor film comprises silicon or germanium.